

Schottky barrier diode

RB425D / RB421D

●Applications

Low power rectification

●Features

- 1) Small surface mounting type. (SMD3)
- 2) High reliability.
- 3) Low reverse current and low forward voltage.

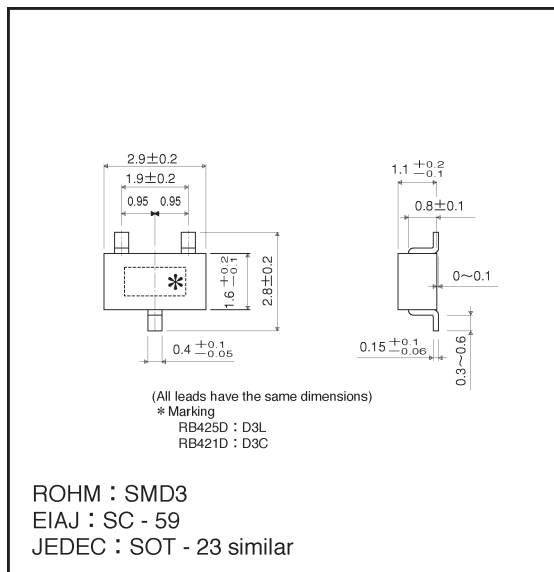
●Construction

Silicon epitaxial planar

●Marking

RB425D	
RB421D	

●External dimensions (Units: mm)

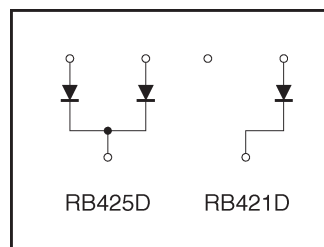


●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	20	V
DC reverse voltage	V_R	10	V
Mean rectifying current	I_O	0.1	A
Peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40~+125	°C

* 60 Hz for 1 

●Equivalent circuits



●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	—	0.45	0.55	V	$I_F=100\text{mA}$
Forward voltage	V_{F2}	—	0.28	0.34	V	$I_F=10\text{mA}$
Reverse current	I_R	—	1.0	30	μA	$V_R=10\text{V}$
Capacitance between terminals	C_T	—	6.0	—	pF	$V_R=10\text{V}, f=1\text{MHz}$

*ESD sensitive product handling required.

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

